TCST1000/TCST2000

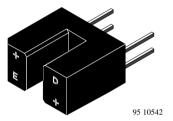
Optoelectronic Interrupter with Aperture

Description

The TCST1000/TCST2000 consist of a phototransistor optically coupled to a gallium arsenide infrared emitting diode in a 6 lead plastic dual inline packages.

The elements are mounted on one leadframe in coplanar technique, providing a fixed distance between input and output for highest safety requirements.





Applications

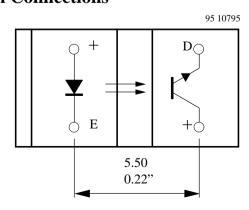
Contactless optoelectronic switch, control and counter.

Features

- Compact construction
- No setting efforts

- 2 case variations
- Polycarbonate case protected against ambient light

Pin Connections



Rev. A1: 25.09.1995



TCST1000/TCST2000

TELEFUNKEN Semiconductors

Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_{R}	6	V
Forward current		I_{F}	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	3	A
Power dissipation	$T_{amb} \le 25^{\circ}C$	P_{V}	100	mW
Junction temperature		T _i	100	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_{C}	100	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	200	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _V	150	mW
Junction temperature		Ti	100	°C

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	250	mW
Ambient temperature range		T _{amb}	-55 to +85	°C
Storage temperature range		T _{stg}	-55 to +100	°C
Soldering temperature, maximal	2 mm from case, $t \le 5$ s	T _{sd}	260	°C

2 (5) Rev. A1: 25.09.1995

TELEFUNKEN Semiconductors

TCST1000/TCST2000

Electrical Characteristics

 $T_{amb} = 25$ °C

Input (Emitter)

Parameters	Test Conditions	Туре	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 60 \text{ mA}$		V_{F}		1.25	1.5	V
Breakdown voltage	$I_R = 100 \mu A$		$V_{(BR)}$	6			V
Junction	$V_R = 0$,		Ci		50		pF
capacitance	f = 1 MHz		J				

Output (Detector)

Parameters	Test Conditions	Туре	Symbol	Min.	Тур.	Max.	Unit
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$		V _{(BR)CEO}	70			V
Emitter collector breakdown voltage	$I_E = 10 \mu A$		V _{(BR)ECO}	7			V
Collector dark current	$V_{CE} = 25 \text{ V},$ $I_F = 0, E = 0$		I _{CEO}			100	nA

Coupler

Parameters	Test Conditions	Туре	Symbol	Min.	Тур.	Max.	Unit
Current Transfer Ratio	$V_{CE} = 5 \text{ V},$ $I_F = 20 \text{ mA}$	TCST1000, TCST2000	CTR	1.25	2.5		%
Collector current	$V_{CE} = 5 \text{ V},$ $I_F = 20 \text{ mA}$	TCST1000, TCST2000	I_{C}	0.25	0.5		mA
Collector emitter saturation voltage	$I_F = 20 \text{ mA},$ $I_C = 25 \mu\text{A}$		V _{CEsat}			0.4	V
Resolution, path of the shutter crossing the radiant sensitive zone	I _{Crel} = 10/90%		S		0.6		mm

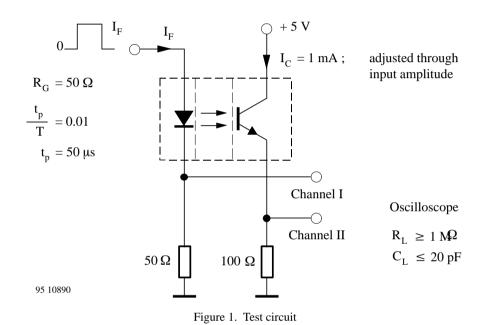
Rev. A1: 25.09.1995

TELEFUNKEN Semiconductors

Switching Characteristics

 $V_S = 5 \text{ V}, I_C = 1 \text{ mA}, R_L = 100 \Omega,$

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Turn-on time		t _{on}		15		μs
Turn-off time		t _{off}		10		μs



4 (5) Rev. A1: 25.09.1995



TELEFUNKEN Semiconductors

TCST1000/TCST2000

Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423

Rev. A1: 25.09.1995 5 (5)